Near- and mid-infrared group IV photonics


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Silicon photonics is seen by many to be the solution to the capacity crunch faced by the communications industry. Global sales of silicon photonics products are predicted to reach US$1 billion by 2020 [1]. The key factors in the predicted success of this technology are integration, and the ability to mass produce products at a low cost, due to its compatibility with CMOS electronics technology. Silicon photonics circuits typically operate at a wavelength of 1.55 µm due to the low loss of optical fibres at this wavelength. To this end, this presentation discusses a novel method of growing single crystal, tuneable composition silicon-germanium-on-insulator by rapid melt growth, with the aim of fabricating extremely low power electro-absorption modulators at a range of wavelengths close to 1.55 µm, enabling dramatic expansion of datalink capacity through the use of wavelength division multiplexing (WDM) [2]. The range of localised uniform composition SiGe layers are formed using only a single growth and single anneal step, as shown in Fig. 1.

Additionally, the extension of silicon photonics into the mid-infrared wavelengths (2 µm and beyond) is discussed. Some basic passive components required for optical circuits are demonstrated, including multi-mode interferometers (MMI), as shown in Fig. 2. Furthermore, the feasibility of fabricating active devices in a Ge-on-Si platform is discussed [3].

References

Presentation Method (Invited/Regular Oral/Poster): Invited